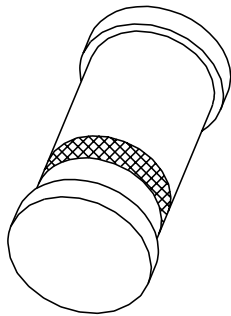


BZV55 series

DATA SHEET



Voltage regulator diodes

Voltage regulator diodes

BZV55 series

FEATURES

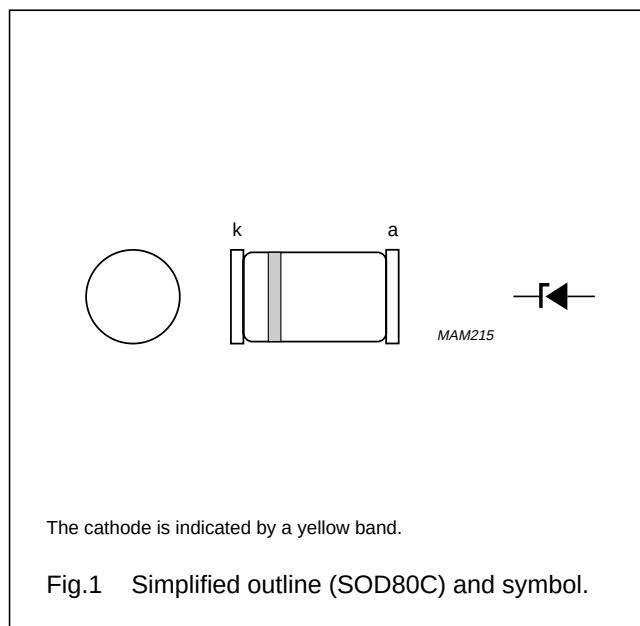
- Total power dissipation: max. 500 mW
- Two tolerance series: $\pm 2\%$, and approx. $\pm 5\%$
- Working voltage range: nom. 2.4 to 75 V (E24 range)
- Non-repetitive peak reverse power dissipation: max. 40 W.

APPLICATIONS

- Low voltage stabilizers or voltage references.

DESCRIPTION

Low-power voltage regulator diodes in small hermetically sealed glass SOD80C SMD packages. The diodes are available in the normalized E24 $\pm 2\%$ (BZV55-B) and approx. $\pm 5\%$ (BZV55-C) tolerance range. The series consists of 37 types with nominal working voltages from 2.4 to 75 V.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_F	continuous forward current		–	250	mA
I_{ZSM}	non-repetitive peak reverse current	$t_p = 100 \mu s$; square wave; $T_j = 25^\circ C$ prior to surge	see Tables 1 and 2		A
P_{tot}	total power dissipation	$T_{amb} \leq 50^\circ C$; note 1	–	400	mW
		tie-point $\leq 50^\circ C$; note 1	–	500	mW
P_{ZSM}	non-repetitive peak reverse power dissipation	$t_p = 100 \mu s$; square wave; $T_j = 25^\circ C$ prior to surge; see Fig.3	–	40	W
T_{stg}	storage temperature		–65	+200	$^\circ C$
T_j	junction temperature		–65	+200	$^\circ C$

Note

1. Device mounted on a ceramic substrate of $10 \times 10 \times 0.6$ mm.

Voltage regulator diodes

BZV55 series

ELECTRICAL CHARACTERISTICS

Total BZV55-B and BZV55-C series

$T_j = 25\text{ }^{\circ}\text{C}$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_F	forward voltage	$I_F = 10\text{ mA}$; see Fig.4	0.9	V
I_R	reverse current			
	BZV55-B/C2V4	$V_R = 1\text{ V}$	50	μA
	BZV55-B/C2V7	$V_R = 1\text{ V}$	20	μA
	BZV55-B/C3V0	$V_R = 1\text{ V}$	10	μA
	BZV55-B/C3V3	$V_R = 1\text{ V}$	5	μA
	BZV55-B/C3V6	$V_R = 1\text{ V}$	5	μA
	BZV55-B/C3V9	$V_R = 1\text{ V}$	3	μA
	BZV55-B/C4V3	$V_R = 1\text{ V}$	3	μA
	BZV55-B/C4V7	$V_R = 2\text{ V}$	3	μA
	BZV55-B/C5V1	$V_R = 2\text{ V}$	2	μA
	BZV55-B/C5V6	$V_R = 2\text{ V}$	1	μA
	BZV55-B/C6V2	$V_R = 4\text{ V}$	3	μA
	BZV55-B/C6V8	$V_R = 4\text{ V}$	2	μA
	BZV55-B/C7V5	$V_R = 5\text{ V}$	1	μA
	BZV55-B/C8V2	$V_R = 5\text{ V}$	700	nA
	BZV55-B/C9V1	$V_R = 6\text{ V}$	500	nA
	BZV55-B/C10	$V_R = 7\text{ V}$	200	nA
	BZV55-B/C11	$V_R = 8\text{ V}$	100	nA
	BZV55-B/C12	$V_R = 8\text{ V}$	100	nA
	BZV55-B/C13	$V_R = 8\text{ V}$	100	nA
	BZV55-B/C15 to BZV55-B/C75	$V_R = 0.7V_{Znom}$	50	nA

Voltage regulator diodes

BZV55 series

Table 1 Per type, BZV55-B/C2V4 to BZV55-B/C24

T_j = 25 °C unless otherwise specified.

BZV55- Bxxx Cxxx	WORKING VOLTAGE V _Z (V) at I _{Ztest} = 5 mA				DIFFERENTIAL RESISTANCE r _{dif} (Ω)				TEMP. COEFF. S _Z (mV/K) at I _{Ztest} = 5 mA (see Figs 5 and 6)			DIODE CAP. C _d (pF) at f = 1 MHz; V _R = 0 V	NON-REPETITIVE PEAK REVERSE CURRENT I _{ZSM} (A) at t _p = 100 μs; T _{amb} = 25 °C
	Tol. ±2% (B)		Tol. approx. ±5% (C)		at I _{Ztest} = 1 mA		at I _{Ztest} = 5 mA						
	MIN.	MAX.	MIN.	MAX.	TYP.	MAX.	TYP.	MAX.	MIN.	TYP.	MAX.	MAX.	MAX.
2V4	2.35	2.45	2.2	2.6	275	600	70	100	−3.5	−1.6	0	450	6.0
2V7	2.65	2.75	2.5	2.9	300	600	75	100	−3.5	−2.0	0	450	6.0
3V0	2.94	3.06	2.8	3.2	325	600	80	95	−3.5	−2.1	0	450	6.0
3V3	3.23	3.37	3.1	3.5	350	600	85	95	−3.5	−2.4	0	450	6.0
3V6	3.53	3.67	3.4	3.8	375	600	85	90	−3.5	−2.4	0	450	6.0
3V9	3.82	3.98	3.7	4.1	400	600	85	90	−3.5	−2.5	0	450	6.0
4V3	4.21	4.39	4.0	4.6	410	600	80	90	−3.5	−2.5	0	450	6.0
4V7	4.61	4.79	4.4	5.0	425	500	50	80	−3.5	−1.4	0.2	300	6.0
5V1	5.00	5.20	4.8	5.4	400	480	40	60	−2.7	−0.8	1.2	300	6.0
5V6	5.49	5.71	5.2	6.0	80	400	15	40	−2.0	1.2	2.5	300	6.0
6V2	6.08	6.32	5.8	6.6	40	150	6	10	0.4	2.3	3.7	200	6.0
6V8	6.66	6.94	6.4	7.2	30	80	6	15	1.2	3.0	4.5	200	6.0
7V5	7.35	7.65	7.0	7.9	30	80	6	15	2.5	4.0	5.3	150	4.0
8V2	8.04	8.36	7.7	8.7	40	80	6	15	3.2	4.6	6.2	150	4.0
9V1	8.92	9.28	8.5	9.6	40	100	6	15	3.8	5.5	7.0	150	3.0
10	9.80	10.20	9.4	10.6	50	150	8	20	4.5	6.4	8.0	90	3.0
11	10.80	11.20	10.4	11.6	50	150	10	20	5.4	7.4	9.0	85	2.5
12	11.80	12.20	11.4	12.7	50	150	10	25	6.0	8.4	10.0	85	2.5
13	12.70	13.30	12.4	14.1	50	170	10	30	7.0	9.4	11.0	80	2.5
15	14.70	15.30	13.8	15.6	50	200	10	30	9.2	11.4	13.0	75	2.0
16	15.70	16.30	15.3	17.1	50	200	10	40	10.4	12.4	14.0	75	1.5
18	17.60	18.40	16.8	19.1	50	225	10	45	12.4	14.4	16.0	70	1.5
20	19.60	20.40	18.8	21.2	60	225	15	55	12.3	15.6	18.0	60	1.5
22	21.60	22.40	20.8	23.3	60	250	20	55	14.1	17.6	20.0	60	1.25
24	23.50	24.50	22.8	25.6	60	250	25	70	15.9	19.6	22.0	55	1.25

Voltage regulator diodes

BZV55 series

Table 2 Per type, BZV55-B/C27 to BZV55-B/C75

$T_j = 25\text{ °C}$ unless otherwise specified.

BZV55- Bxxx Cxxx	WORKING VOLTAGE V _Z (V) at I _{Ztest} = 2 mA				DIFFERENTIAL RESISTANCE r _{diff} (Ω)				TEMP. COEFF. S _Z (mV/K) at I _{Ztest} = 2 mA (see Figs 5 and 6)			DIODE CAP. C _d (pF) at f = 1 MHz; V _R = 0 V	NON-REPETITIVE PEAK REVERSE CURRENT I _{ZSM} (A) at t _p = 100 μs; T _{amb} = 25 °C
	Tol. ±2% (B)		Tol. approx. ±5% (C)		at I _{Ztest} = 0.5 mA		at I _{Ztest} = 2 mA						
	MIN.	MAX.	MIN.	MAX.	TYP.	MAX.	TYP.	MAX.	MIN.	TYP.	MAX.	MAX.	MAX.
27	26.50	27.50	25.1	28.9	65	300	25	80	18.0	22.7	25.3	50	1.0
30	29.40	30.60	28.0	32.0	70	300	30	80	20.6	25.7	29.4	50	1.0
33	32.30	33.70	31.0	35.0	75	325	35	80	23.3	28.7	33.4	45	0.9
36	35.30	36.70	34.0	38.0	80	350	35	90	26.0	31.8	37.4	45	0.8
39	38.20	39.80	37.0	41.0	80	350	40	130	28.7	34.8	41.2	45	0.7
43	42.10	43.90	40.0	46.0	85	375	45	150	31.4	38.8	46.6	40	0.6
47	46.10	47.90	44.0	50.0	85	375	50	170	35.0	42.9	51.8	40	0.5
51	50.00	52.00	48.0	54.0	90	400	60	180	38.6	46.9	57.2	40	0.4
56	54.90	57.10	52.0	60.0	100	425	70	200	42.2	52.0	63.8	40	0.3
62	60.80	63.20	58.0	66.0	120	450	80	215	58.8	64.4	71.6	35	0.3
68	66.60	69.40	64.0	72.0	150	475	90	240	65.6	71.7	79.8	35	0.25
75	73.50	76.50	70.0	79.0	170	500	95	255	73.4	80.2	88.6	35	0.2

Voltage regulator diodes

BZV55 series

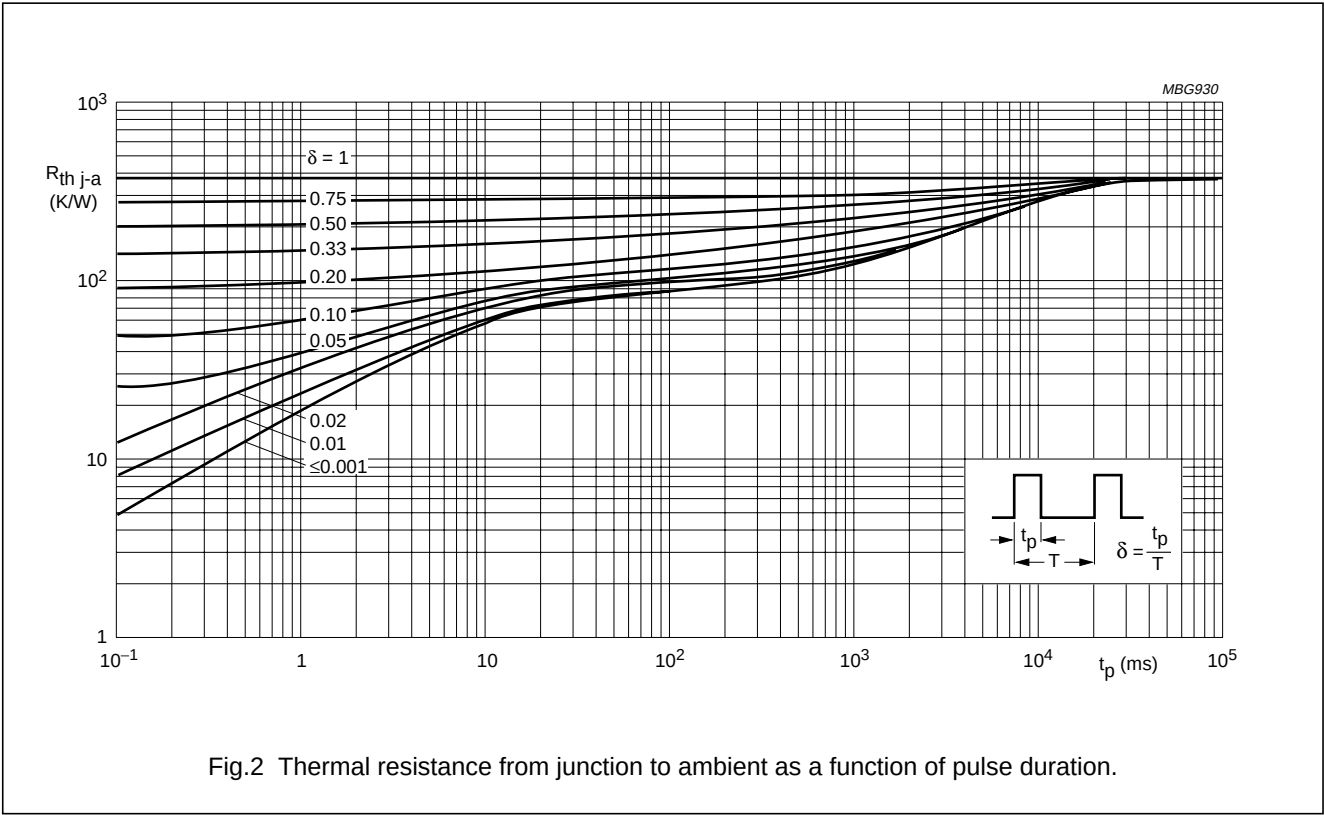
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-t_p}$	thermal resistance from junction to tie-point		300	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	see Fig.2 and note 1	380	K/W

Note

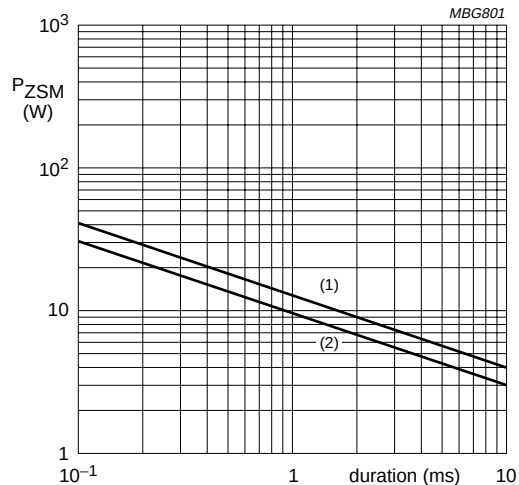
1. Device mounted on a ceramic substrate of $10 \times 10 \times 0.6$ mm.

GRAPHICAL DATA



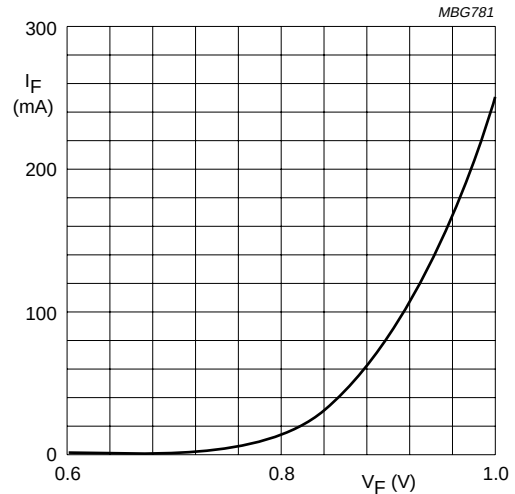
Voltage regulator diodes

BZV55 series



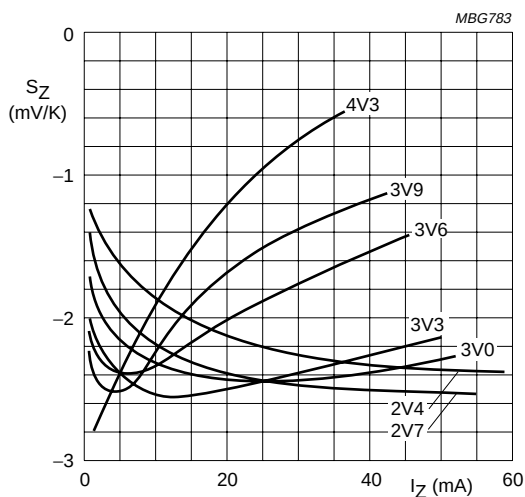
- (1) $T_j = 25\text{ °C}$ (prior to surge).
(2) $T_j = 150\text{ °C}$ (prior to surge).

Fig.3 Maximum permissible non-repetitive peak reverse power dissipation versus duration.



$T_j = 25\text{ °C}$.

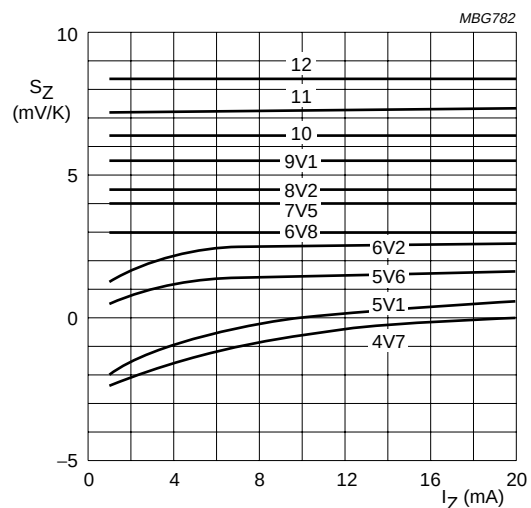
Fig.4 Typical forward current as a function of forward voltage.



BZV55-B/C2V4 to BZV55-B/C4V3.

$T_j = 25\text{ to }150\text{ °C}$.

Fig.5 Temperature coefficient as a function of working current; typical values.



BZV55-B/C4V7 to BZV55-B/C12.

$T_j = 25\text{ to }150\text{ °C}$.

Fig.6 Temperature coefficient as a function of working current; typical values.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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